

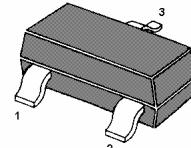
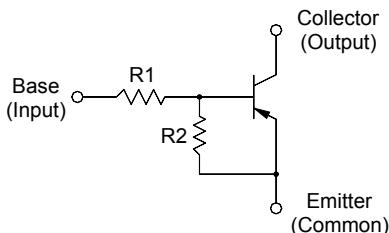
MMBTRA116SS...MMBTRA122SS

PNP Silicon Epitaxial Planar Transistor

for switching, interface circuit and drive circuit applications

Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



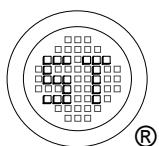
1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Resistor Values

Type	R1 (KΩ)	R2 (KΩ)
MMBTRA116SS	1	10
MMBTRA117SS	2.2	2.2
MMBTRA118SS	2.2	10
MMBTRA119SS	4.7	10
MMBTRA120SS	10	4.7
MMBTRA121SS	47	10
MMBTRA122SS	100	100

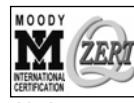
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Output Voltage	$-V_O$	50	V
Input Voltage	MMBTRA116SS	- 10, 5	V
	MMBTRA117SS	- 12, 10	
	MMBTRA118SS	- 12, 5	
	MMBTRA119SS	- 20, 7	
	MMBTRA120SS	- 30, 10	
	MMBTRA121SS	- 40, 15	
	MMBTRA122SS	- 40, 10	
Output Current	$-I_O$	100	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	- 55 to + 150	°C



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ISO/TS 16949 : 2002
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ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098

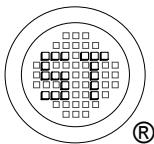
Dated : 29/10/2007

MMBTRA116SS...MMBTRA122SS

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_O = 5\text{ V}$, $-I_O = 5\text{ mA}$ at $-V_O = 5\text{ V}$, $-I_O = 20\text{ mA}$ at $-V_O = 5\text{ V}$, $-I_O = 10\text{ mA}$ at $-V_O = 5\text{ V}$, $-I_O = 10\text{ mA}$ at $-V_O = 5\text{ V}$, $-I_O = 10\text{ mA}$ at $-V_O = 5\text{ V}$, $-I_O = 5\text{ mA}$ at $-V_O = 5\text{ V}$, $-I_O = 5\text{ mA}$	G_I	33	-	-	-
		20	-	-	-
		33	-	-	-
		30	-	-	-
		24	-	-	-
		33	-	-	-
		62	-	-	-
Output Cutoff Current at $-V_O = 50\text{ V}$	$-I_{O(OFF)}$	-	-	500	nA
Input Current at $-V_I = 5\text{ V}$	$-I_I$	-	-	7.2	mA
		-	-	3.8	
		-	-	3.8	
		-	-	1.8	
		-	-	0.88	
		-	-	0.16	
		-	-	0.15	
Output Voltage at $-I_O = 10\text{ mA}$, $-I_I = 0.5\text{ mA}$ at $-I_O = 10\text{ mA}$, $-I_I = 0.5\text{ mA}$ at $-I_O = 10\text{ mA}$, $-I_I = 0.5\text{ mA}$ at $-I_O = 10\text{ mA}$, $-I_I = 0.5\text{ mA}$ at $-I_O = 10\text{ mA}$, $-I_I = 0.5\text{ mA}$ at $-I_O = 10\text{ mA}$, $-I_I = 0.5\text{ mA}$ at $-I_O = 5\text{ mA}$, $-I_I = 0.25\text{ mA}$	$-V_{O(ON)}$	-	-	0.3	V
		-	-	0.3	
		-	-	0.3	
		-	-	0.3	
		-	-	0.3	
		-	-	0.3	
		-	-	0.3	
Input Voltage (ON) at $-V_O = 0.3\text{ V}$, $-I_O = 20\text{ mA}$ at $-V_O = 0.3\text{ V}$, $-I_O = 20\text{ mA}$ at $-V_O = 0.3\text{ V}$, $-I_O = 20\text{ mA}$ at $-V_O = 0.3\text{ V}$, $-I_O = 20\text{ mA}$ at $-V_O = 0.3\text{ V}$, $-I_O = 2\text{ mA}$ at $-V_O = 0.3\text{ V}$, $-I_O = 2\text{ mA}$ at $-V_O = 0.3\text{ V}$, $-I_O = 1\text{ mA}$	$-V_{I(ON)}$	-	-	3	V
		-	-	3	
		-	-	3	
		-	-	2.5	
		-	-	3	
		-	-	5	
		-	-	3	
Input Voltage (OFF) at $-V_{CC} = 5\text{ V}$, $-I_O = 100\text{ }\mu\text{A}$	$-V_{I(OFF)}$	0.3	-	-	V
		0.5	-	-	
		0.3	-	-	
		0.3	-	-	
		0.8	-	-	
		1	-	-	
		0.5	-	-	
Transition Frequency at $-V_O = 10\text{ V}$, $-I_O = 5\text{ mA}$	$f_T^{(1)}$	-	250	-	MHz

⁽¹⁾ Characteristic of transistor only.



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